

-20V P-Channel Plastic-Encapsulate MOSFET

MAIN CHARACTERISTICS

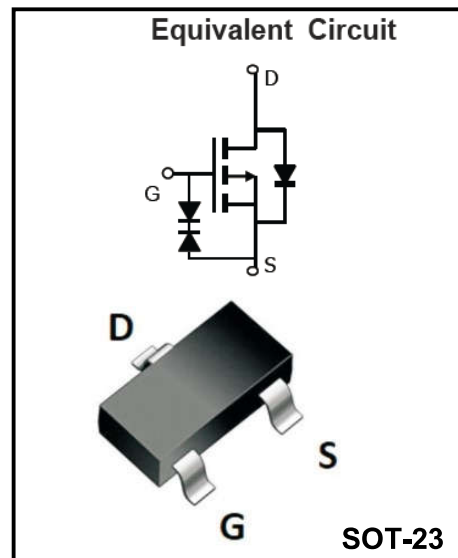
I_D	-4.2A
V_{DSS}	-20V
$R_{DS(on)-typ}(@V_{GS}=4.5V)$	<50mΩ (Type:37 mΩ)
$R_{DS(on)-typ}(@V_{GS}=2.5V)$	<60mΩ (Type:45 mΩ)
$R_{DS(on)-typ}(@V_{GS}=1.8V)$	<73mΩ (Type:56 mΩ)

Features

- ♦Excellent $R_{DS(on)}$, low gate charge, low gate voltages
- ♦Load Switch and in PWM applications.
- ♦ESD protected.

Mechanical Data

- ♦SOT-23 Small Outline Plastic Package.
- ♦Epoxy UL: 94V-0.
- ♦Mounting Position: Any.



Marking Code

YFW3415A

R15

Maximum Ratings & Thermal Characteristics

(Ratings at 25°C ambient temperature unless otherwise specified.)

Parameters	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	-20	V
Gate-Source Voltage	V_{GS}	±8	V
Continuous Drain Current	I_D	-4.2	A
Power Dissipation	P_D	350	mW
Junction Temperature	T_J	150	°C
Storage Temperature	T_{stg}	-50-+150	°C
Thermal Resistance From Junction to Ambient	$R_{\theta JA}$	357	°C/W

Electrical Characteristics

(Ratings at 25°C ambient temperature unless otherwise specified).

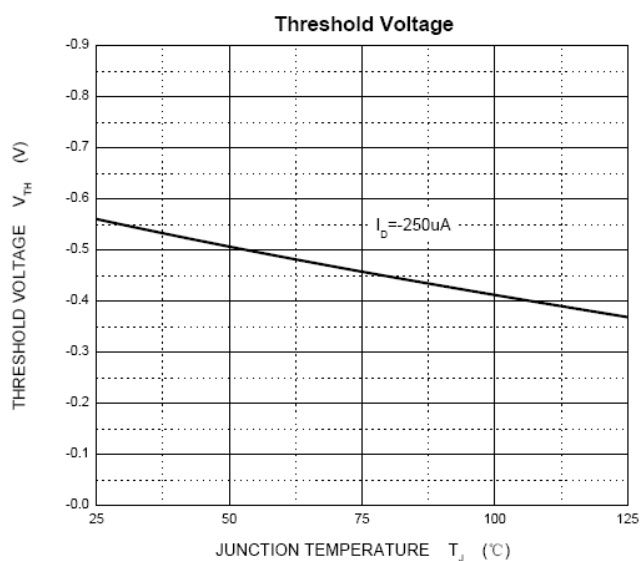
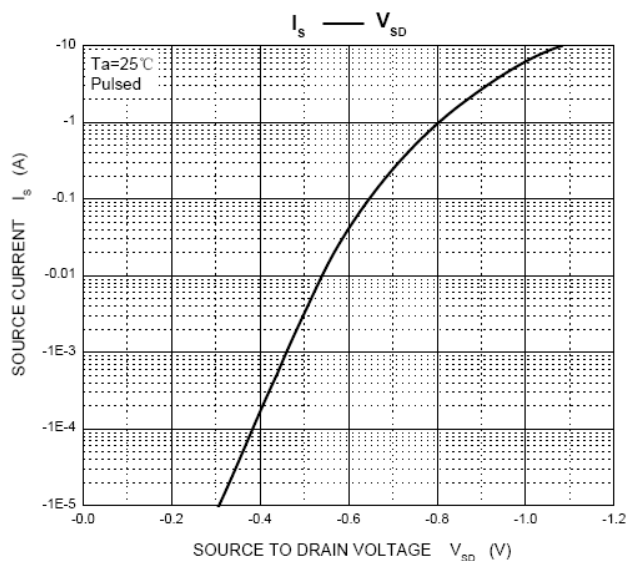
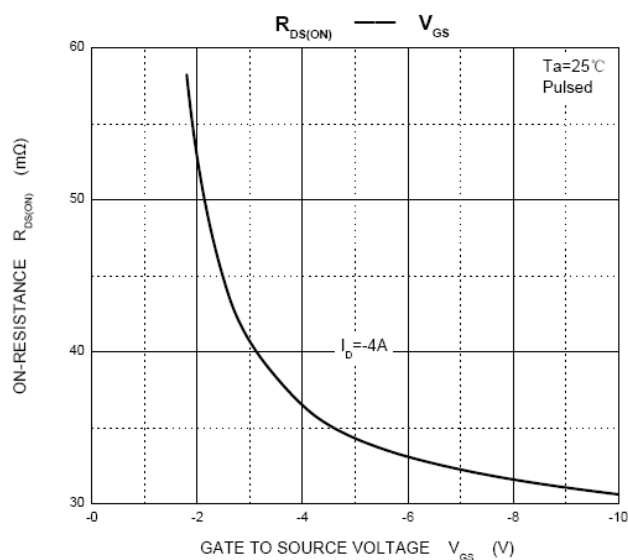
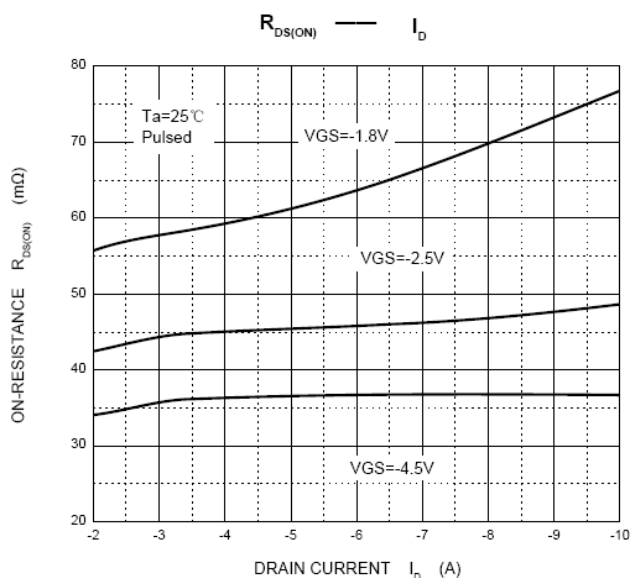
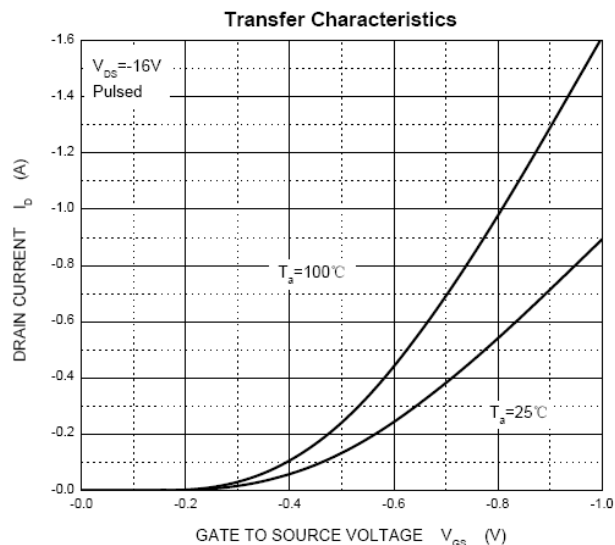
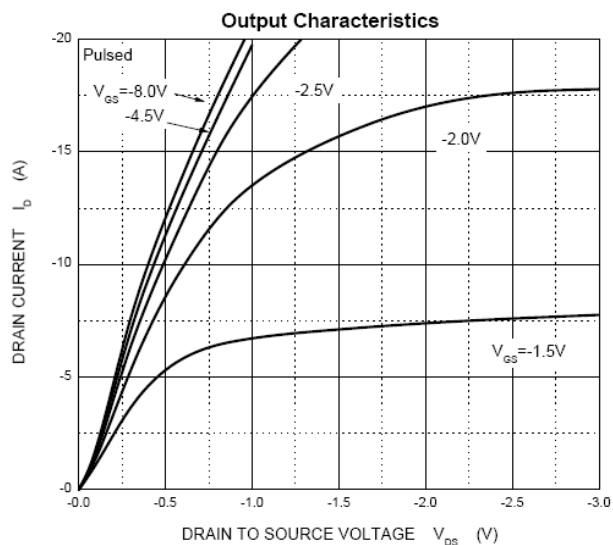
Parameter	Symbols	Test Condition	Limits			Unit
			Min	Typ	Max	
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=-250\mu A$	-20			V
Gate-Threshold voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-250\mu A$	-0.3	-0.56	-1.0	V
Gate-body Leakage	I_{GSS}	$V_{DS}=0V, V_{GS}=\pm 8V$			± 10	μA
		$V_{DS}=0V, V_{GS}=\pm 4.5V$			± 1	
Zero Gate Voltage Drain current	I_{DSS}	$V_{DS}=-16V, V_{GS}=0V$			-1	
Drain-Source On-Resistance(a)	$R_{DS(ON)}$	$V_{GS}=-4.5V, I_D=-4A$		37	50	m Ω
		$V_{GS}=-2.5V, I_D=-4A$		45	60	
		$V_{GS}=-1.8V, I_D=-2A$		56	73	
Forward trans conductance(b)	g_{fs}	$V_{DS}=-5V, I_D=-4A$	8			S
Input capacitance	C_{iss}	$V_{DS}=-10V, V_{GS}=0V, f=1MHz$		1450		pF
Output capacitance	C_{oss}			205		
Reverse Transfer capacitance	C_{rss}			160		
Total gate charge	Q_g	$V_{DS}=-10V, V_{GS}=-4.5V, I_D=-4A$		17.2		nC
Gate-source charge	Q_{gs}			1.3		
Gate-drain charge	Q_{gd}			4.5		
Gate resistance	R_g	$V_{DS}=0V, V_{GS}=0V, f=1MHz$		6.5		Ω
Turn-on Time	$t_{d(on)}$	$V_{DD}=-10V, R_L=2.5\Omega, V_{GEN}=-4.5V, R_{GEN}=3\Omega$		9.5		ns
Rise time	T_r			17		
Turn-off Time	$t_{d(off)}$			94		
Fall time	t_f			35		
Body diode voltage(b)	V_{SD}	$I_S=-1A, V_{GS}=0V$			-1.0	V

Notes: a. Repetitive rating, pulse width limited by junction temperature.

B. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.

b. These parameters have no way to verify.

Typical characteristics



Ordering information

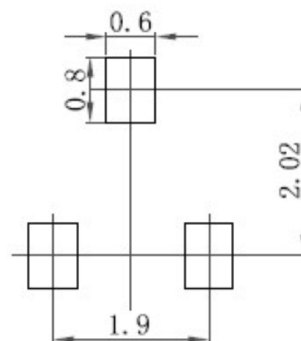
Package	Packing Description	Base Quantity	Packing Quantity
SOT-23	Tape/Reel, 7" reel	3000pcs/Reel	24000PCS/Box 120000PCS/Carton

Package Dimensions

SOT-23

Dim.	Millimeter (mm)		mil	
	Min.	Max.	Min.	Max.
A	0.9	1.15	35	45
A1	0.1		3.9	
bp	0.38	0.48	15	19
C	0.09	0.15	3.54	5.9
D	2.8	3.0	110	118
E	1.2	1.4	47	55
E	1.9		75	
E1	0.95		37	
HE	2.1	2.55	83	100
Lp	0.15	0.45	5.9	18
Q	0.45	0.55	18	22
v	0.2		7.9	
W	0.1		4	

The recommended mounting pad size



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